

<b>Session Title:</b>	<b>[TA1] Nanoscale Thin Film Deposition III</b>
<b>Session Date:</b>	<b>November 15 (Tue.), 2022</b>
<b>Session Time:</b>	<b>09:30-11:00</b>
<b>Session Room:</b>	<b>Room A (Capri Room, 2F)</b>
<b>Session Chair:</b>	<b>Prof. Han-Bo-Ram Lee (Incheon Nat'l Univ., Korea)</b>

**[TA1-1] 09:30-09:50**

**Crystallinity and Interfacial Layer Modulation by Utilizing the Atomic Layer Deposition Process for the Next-Generation DRAM Capacitor Applications**

**Woojin Jeon (Kyung Hee Univ., Korea)**

**[TA1-2] 09:50-10:10**

**Atomic Layer Deposition of SrO for High-k Dielectric Thin Films**

**Woongkyu Lee (Soongsil Univ., Korea)**

**[TA1-3] 10:10-10:30**

**Physical Scaling-Down of Hafnia-Based Ferroelectric Thin Films**

**Kun Yang, Se Hyun Kim, Ju Yong Park, and Min Hyuk Park (Seoul Nat'l Univ., Korea)**

**[TA1-4] [Invited] 10:30-11:00**

**Optimization of Semiconductor Device Characteristics Using Nano-Scale Thin Film Deposition**

**HanJin Lim, Jae Hyoung Choi, Gihee Cho, Jaewan Chang, Jong-Min Park, Young Geun Park, Hyung-Suk Jung, Bongjin Kuh, and Jongmyeong Lee (Samsung Electronics Co., Ltd., Korea)**